

Dual P-channel Enhancement Mode Power MOSFET

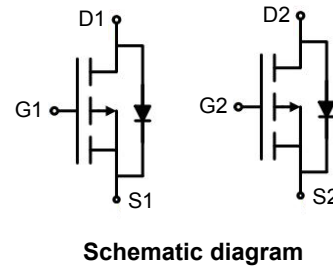
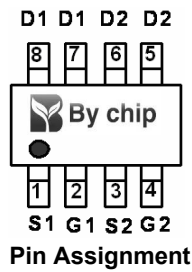
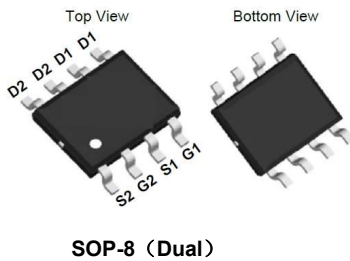
Features

- $V_{DS} = -60V$, $I_D = -5.3A$
 $R_{DS(ON)} < 54m\Omega$ @ $V_{GS} = -10V$
 $R_{DS(ON)} < 60m\Omega$ @ $V_{GS} = -4.5V$

General Features

- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free and Green Available

100% UIS TESTED!
100% ΔV_{ds} TESTED!



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ C$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ C$)	I_D	$T_C = 25^\circ C$ - 5.3 ^e	A
		$T_C = 70^\circ C$ - 5.0 ^e	
		$T_A = 25^\circ C$ - 5.3 ^{a, b}	
		$T_A = 70^\circ C$ - 5.0 ^{a, b}	
Pulsed Drain Current	I_{DM}	- 32 ^e	
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ C$ - 4.1	
		$T_A = 25^\circ C$ - 2.0 ^{a, b}	
Avalanche Current	I_{AS}	- 20	
Single-Pulse Avalanche Energy	E_{AS}	20	mJ
Maximum Power Dissipation	P_D	$T_C = 25^\circ C$ 4.0	W
		$T_C = 70^\circ C$ 2.5	
		$T_A = 25^\circ C$ 2.0 ^{a, b}	
		$T_A = 70^\circ C$ 1.4 ^{a, b}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	38	50	$^\circ C/W$
Maximum Junction-to-Foot	R_{thJF}	20	25	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under Steady State conditions is $85^\circ C/W$.
- Based on $T_C = 25^\circ C$.
- Limited by package.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 31		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			4.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1.0		- 3.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 10 V, V _{GS} = - 10 V	- 30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 5 A		0.054		Ω
		V _{GS} = - 4.5 V, I _D = - 4.5 A		0.060		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 5 A		23		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		1345		pF
Output Capacitance	C _{oss}			210		
Reverse Transfer Capacitance	C _{rss}			180		
Total Gate Charge	Q _g	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 5 A		32	50	nC
		V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 5 A		15	25	
Gate-Source Charge	Q _{gs}			4		
Gate-Drain Charge	Q _{gd}			7.5		
Gate Resistance	R _g	f = 1 MHz		5.8		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 15 Ω I _D ≡ - 1 A, V _{GEN} = - 10 V, R _g = 1 Ω		10	15	ns
Rise Time	t _r			8	15	
Turn-Off DelayTime	t _{d(off)}			45	70	
Fall Time	t _f			12	25	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 15 Ω I _D ≡ - 1 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		42	70	
Rise Time	t _r			35	60	
Turn-Off DelayTime	t _{d(off)}			40	70	
Fall Time	t _f			16	30	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.1	A
Pulse Diode Forward Current	I _{SM}				- 32	
Body Diode Voltage	V _{SD}	I _S = - 2 A, V _{GS} = 0 V		- 0.75	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 2 A, dI/dt = 100 A/μs, T _J = 25 °C		34	60	ns
Body Diode Reverse Recovery Charge	Q _{rr}			22	40	nC
Reverse Recovery Fall Time	t _a			11		ns
Reverse Recovery Rise Time	t _b			23		

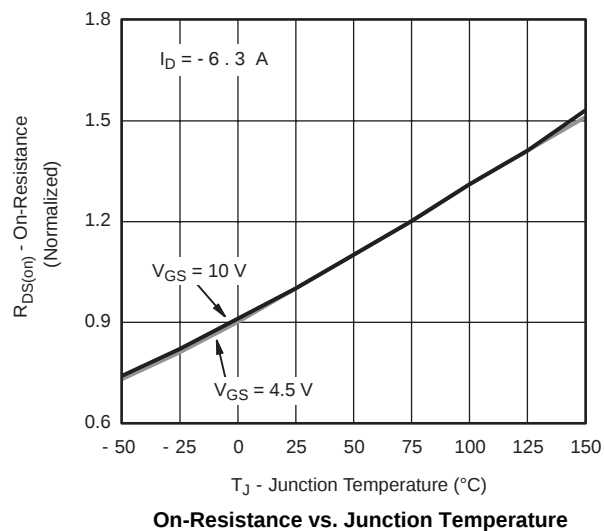
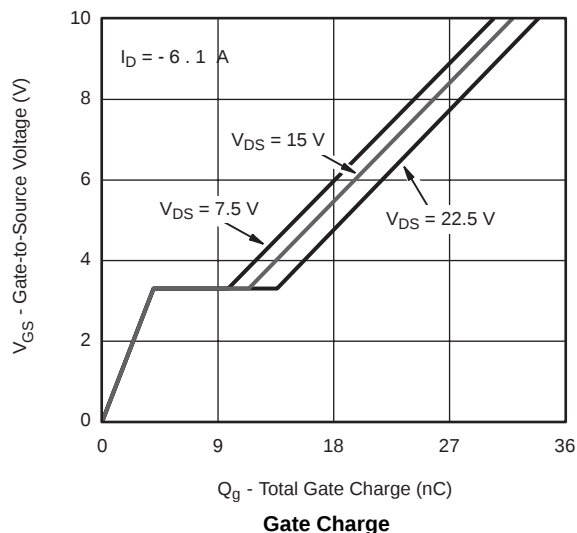
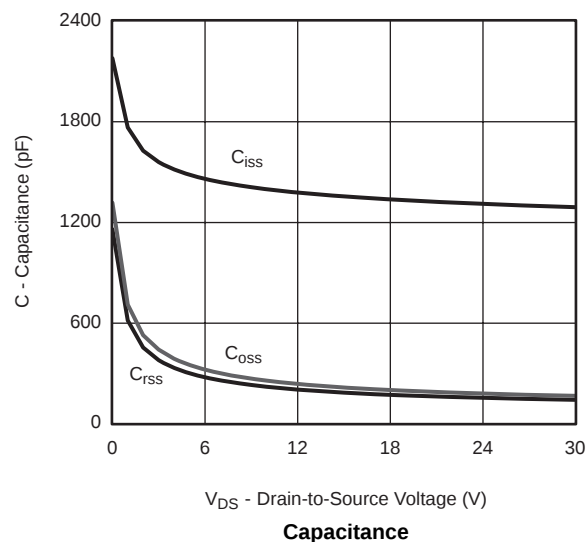
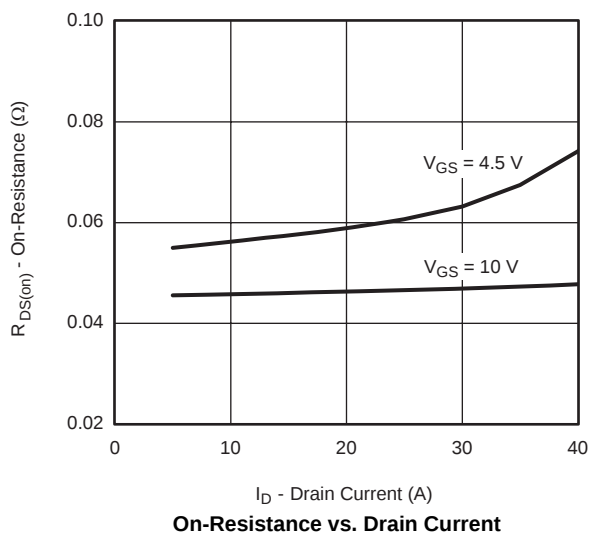
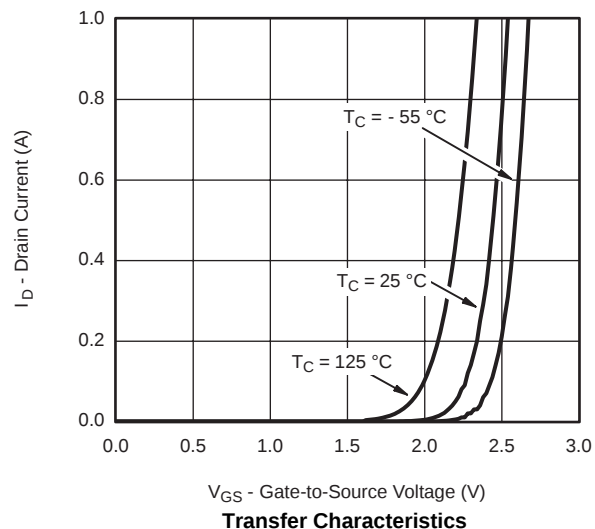
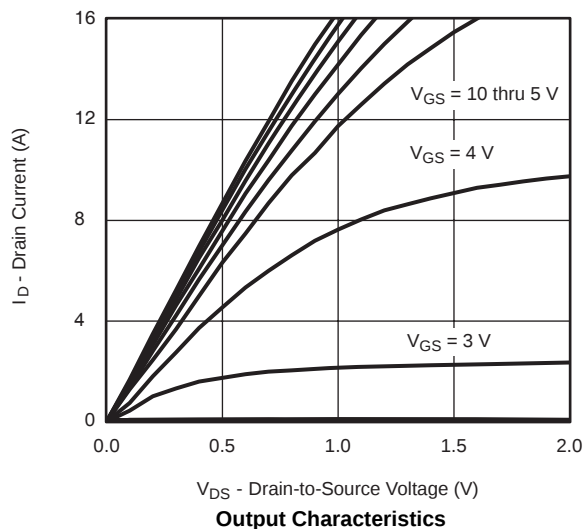
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

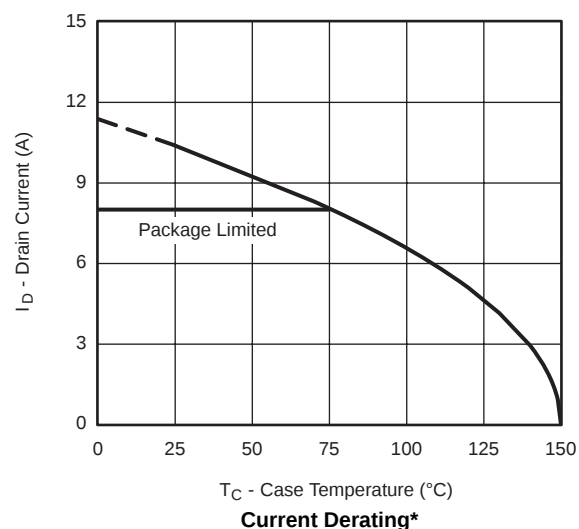
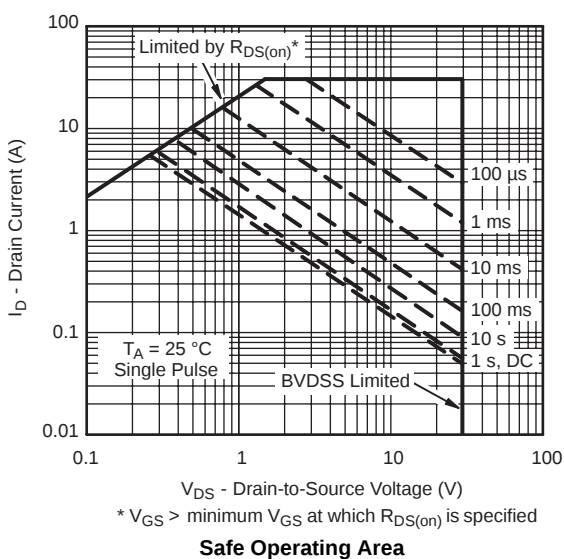
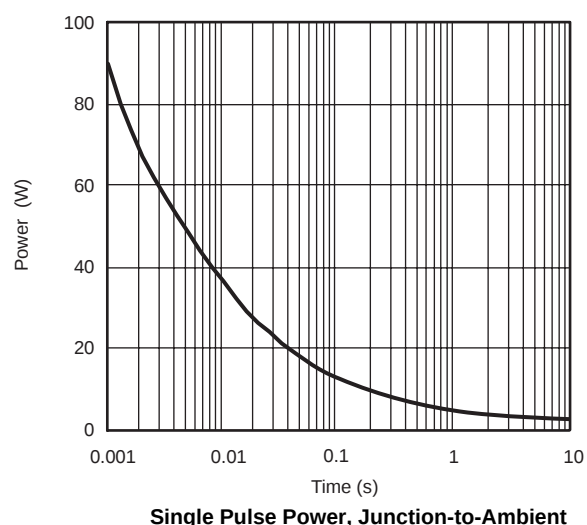
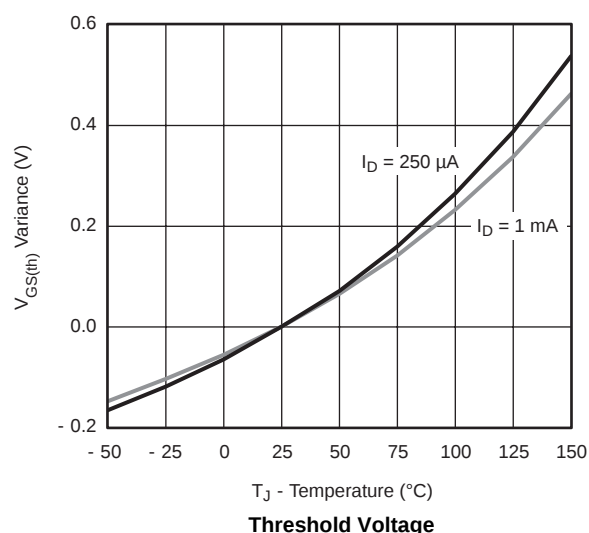
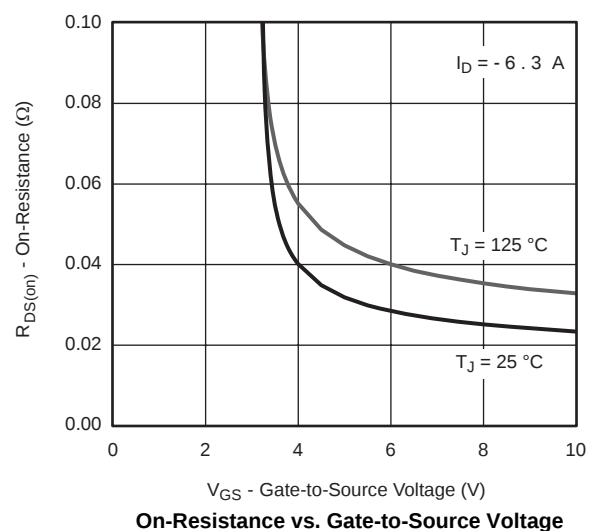
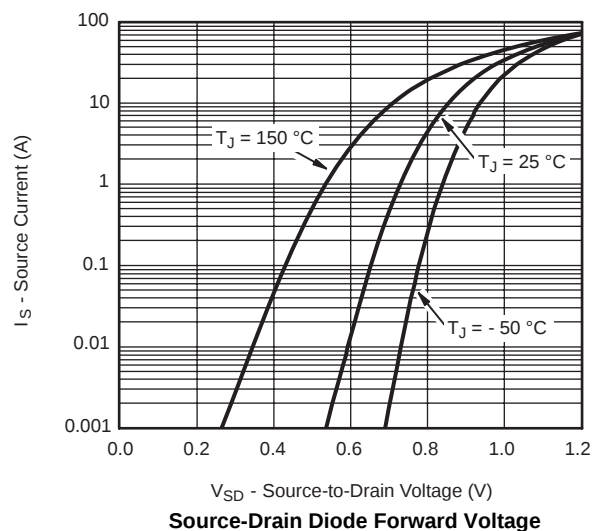
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

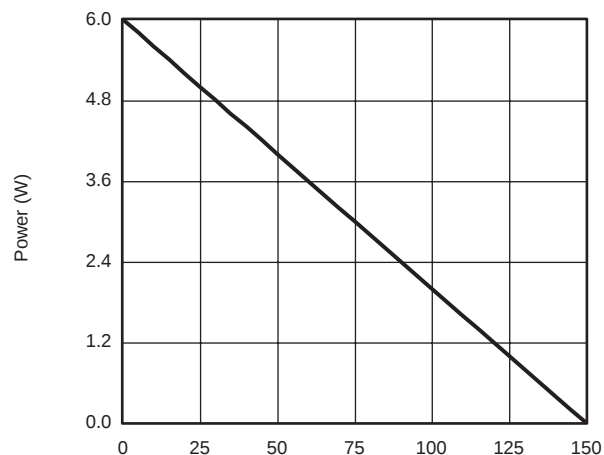
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

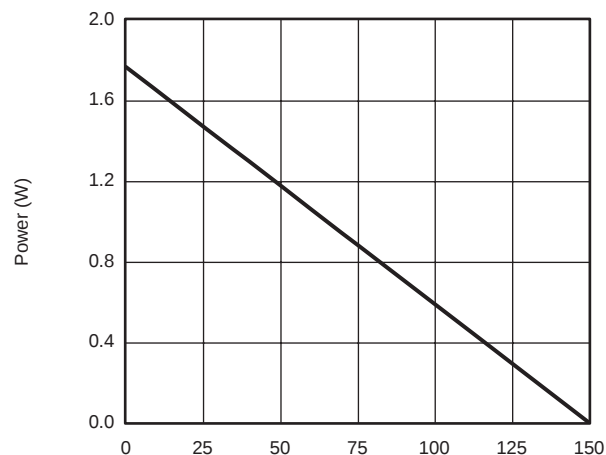


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



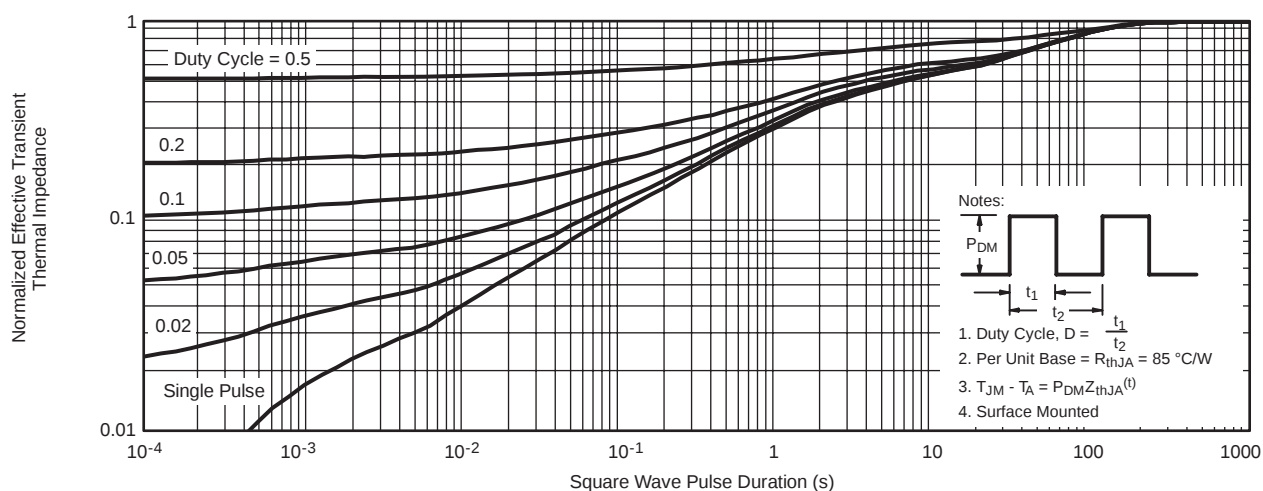
T_C - Case Temperature (°C)

Power, Junction-to-Foot

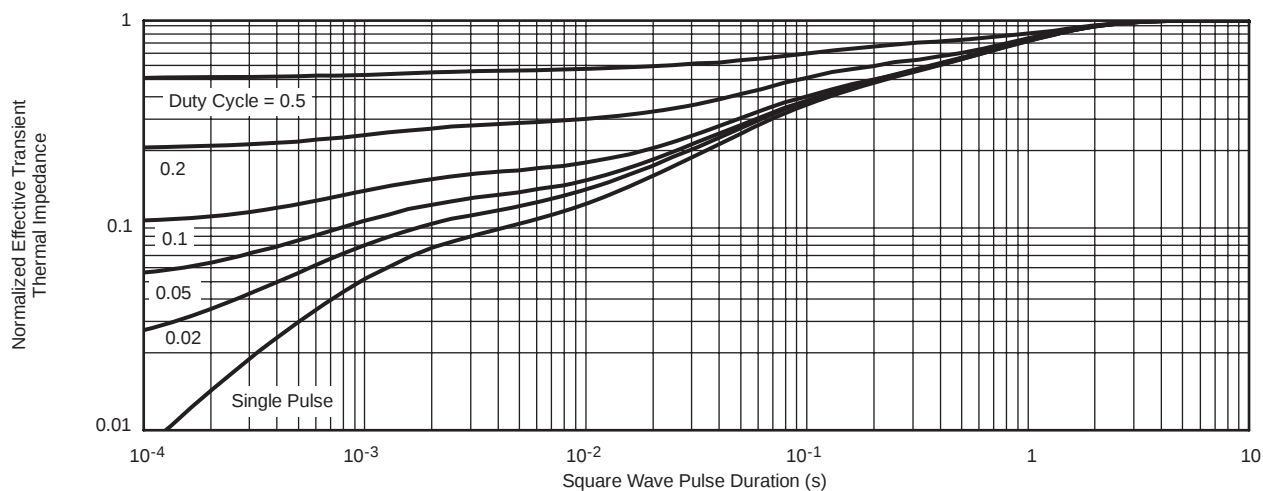


T_A - Ambient Temperature (°C)

Power Derating, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot